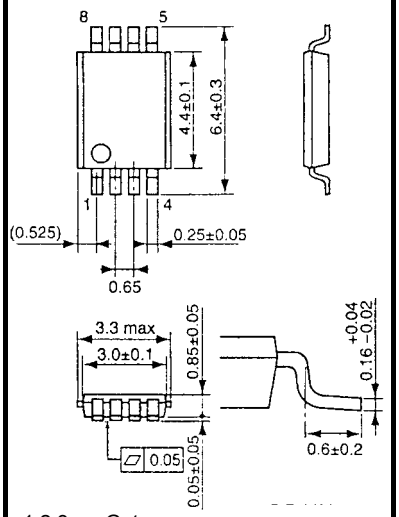
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

TPCS8006

High Speed Switching Applications
Switching Regulator Applications
DC-DC Converters

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 0.8 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 1.6 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 250 V)
- Enhancement-model: V_{th} = 1.5~3.5 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



1.2.3. Gate
4 Source
5.6.7.8 Drain

JEDEC	—
JEITA	—
TOSHIBA	2-3R1F

Weight: 0.035 g (typ.)

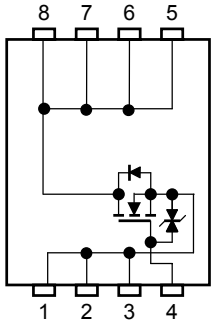
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	250	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	250	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	1.1	A
	Pulse (Note 1)	I_{DP}	4.4	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.5	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	0.6	
Single pulse avalanche energy(Note3)		E_{AS}	0.07	mJ
Avalanche current		I_{AR}	1.1	A
Repetitive avalanche energy (Note2a, Note 4)		E_{AR}	0.15	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: For (Note 1), (Note 2), (Note 3) and (Note 4), please refer to the next page.

This transistor is an electrostatic sensitive device. Please handle with caution.

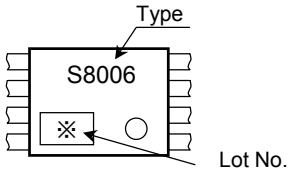
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	83.3	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	208	°C/W

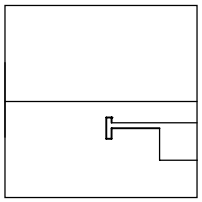
Marking (Note 5)



Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:

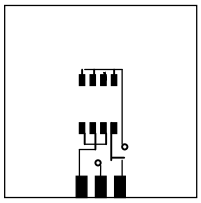
a) Device mounted on a glass-epoxy board (a)



FR-4
25.4 × 25.4 × 0.8
(unit: mm)

(a)

b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(unit: mm)

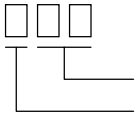
(b)

Note 3: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = 1.1 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: ○ on lower right of the marking indicates Pin 1.

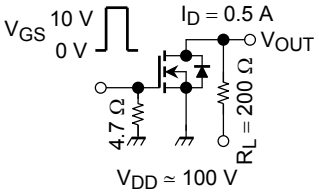
※ Weekly code: (Three digits)



Week of manufacture
(01 for first week of year, continues up to 52 or 53)

Year of manufacture
(One low-order digits of calendar year)

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-OFF current		I_{DSS}	V_{DS} = 250 V, V_{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	250	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 0.5 A	—	0.8	1.0	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 0.5 A	0.7	1.6	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	380	—	pF
Reverse transfer capacitance		C_{rss}		—	32	—	pF
Output capacitance		C_{oss}		—	105	—	pF
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	11	—	ns
	Turn-ON time	t_{on}		—	20	—	
	Fall time	t_f		—	15	—	
	Turn-OFF time	t_{off}		—	45	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ 200V, V_{GS} = 10 V, I_D = 1.1 A	—	11	—	nC
Gate-source charge		Q_{gs}		—	7	—	nC
Gate-drain (“miller”) charge		Q_{gd}		—	4	—	nC

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current (pulse) (Note 1)	I_{DRP}	—	—	—	4.4	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 1.1 A, V_{GS} = 0 V	—	—	−2.0	V
Reverse recovery time	t_{rr}	I_{DR} = 1.1 A, V_{GS} = 0 V, dI_{DR}/dt = 100 A/μs	—	100	—	ns
Reverse recovery charge	Q_{rr}		—	320	—	nC

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